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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, IR, POR, PWM, WDT
Number of I/O	41
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8l151c4u6tr

Contents

2.1 Device overview

Table 2. Medium-density STM8L151x4/6 and STM8L152x4/6 low-power device features and peripheral counts

Features		STM8L151Gx		STM8L15xKx		STM8L15xCx	
Flash (Kbyte)		16	32	16	32	16	32
Data EEPROM (Kbyte)		1					
RAM (Kbyte)		2					
LCD		No		4x17 (1)		4x28 (1)	
Timers	Basic	1 (8-bit)					
	General purpose	2 (16-bit)					
	Advanced control	1 (16-bit)					
Communication interfaces	SPI	1					
	I2C	1					
	USART	1					
GPIOs		26(3)		30 (2)(3) or 29 (1)(3)		41(3)	
12-bit synchronized ADC (number of channels)		1 (18)		1 (22 (2) or 21 (1))		1 (25)	
12-Bit DAC (number of channels)		1 (1)					
Comparators COMP1/COMP2		2					
Others		RTC, window watchdog, independent watchdog, 16-MHz and 38-kHz internal RC, 1- to 16-MHz and 32-kHz external oscillator					
CPU frequency		16 MHz					
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power down)					
Operating temperature		-40 to +85 °C/ -40 to +105 °C / -40 to +125 °C					
Packages		UFQFPN28 (4x4; 0.6 mm thickness) WLCSP28		LQFP32(7x7) UFQFPN32 (5x5; 0.6 mm thickness)		LQFP48 UFQFPN48 (4x4; 0.6 mm thickness)	

1. STM8L152xx versions only
2. STM8L151xx versions only
3. The number of GPIOs given in this table includes the NRST/PA1 pin but the application can use the NRST/PA1 pin as general purpose output only (PA1).

3.3 Reset and supply management

3.3.1 Power supply scheme

The device requires a 1.65 V to 3.6 V operating supply voltage (V_{DD}). The external power supply pins must be connected as follows:

- V_{SS1}; V_{DD1} = 1.8 to 3.6 V, down to 1.65 V at power down: external power supply for I/Os and for the internal regulator. Provided externally through V_{DD1} pins, the corresponding ground pin is V_{SS1}.
- $V_{SSA;}$ V_{DDA} = 1.8 to 3.6 V, down to 1.65 V at power down: external power supplies for analog peripherals (minimum voltage to be applied to V_{DDA} is 1.8 V when the ADC1 is used). V_{DDA} and V_{SSA} must be connected to V_{DD1} and V_{SS1}, respectively.
- V_{SS2}; V_{DD2} = 1.8 to 3.6 V, down to 1.65 V at power down: external power supplies for I/Os. V_{DD2} and V_{SS2} must be connected to V_{DD1} and V_{SS1}, respectively.
- V_{REF+}; V_{REF-} (for ADC1): external reference voltage for ADC1. Must be provided externally through V_{REF+} and V_{REF-} pin.
- V_{REF+} (for DAC): external voltage reference for DAC must be provided externally through V_{REF+}.

3.3.2 Power supply supervisor

The device has an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR), coupled with a brownout reset (BOR) circuitry. At power-on, BOR is always active, and ensures proper operation starting from 1.8 V. After the 1.8 V BOR threshold is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable BOR permanently (in which case, the V_{DD} min value at power down is 1.65 V).

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Halt mode, it is possible to automatically switch off the internal reference voltage (and consequently the BOR) in Halt mode. The device remains under reset when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR}, without the need for any external reset circuit.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The medium-density STM8L151x4/6 and STM8L152x4/6 embeds an internal voltage regulator for generating the 1.8 V power supply for the core and peripherals.

This regulator has two different modes:

- Main voltage regulator mode (MVR) for Run, Wait for interrupt (WFI) and Wait for event (WFE) modes.
- Low power voltage regulator mode (LPVR) for Halt, Active-halt, Low power run and Low power wait modes.

When entering Halt or Active-halt modes, the system automatically switches from the MVR to the LPVR in order to reduce current consumption.

3.14.2 16-bit general purpose timers

- 16-bit autoreload (AR) up/down-counter
- 7-bit prescaler adjustable to fixed power of 2 ratios (1…128)
- 2 individually configurable capture/compare channels
- PWM mode
- Interrupt capability on various events (capture, compare, overflow, break, trigger)
- Synchronization with other timers or external signals (external clock, reset, trigger and enable)

3.14.3 8-bit basic timer

The 8-bit timer consists of an 8-bit up auto-reload counter driven by a programmable prescaler. It can be used for timebase generation with interrupt generation on timer overflow or for DAC trigger generation.

3.15 Watchdog timers

The watchdog system is based on two independent timers providing maximum security to the applications.

3.15.1 Window watchdog timer

The window watchdog (WWDG) is used to detect the occurrence of a software fault, usually generated by external interferences or by unexpected logical conditions, which cause the application program to abandon its normal sequence.

3.15.2 Independent watchdog timer

The independent watchdog peripheral (IWDG) can be used to resolve processor malfunctions due to hardware or software failures.

It is clocked by the internal LSI RC clock source, and thus stays active even in case of a CPU clock failure.

3.16 Beeper

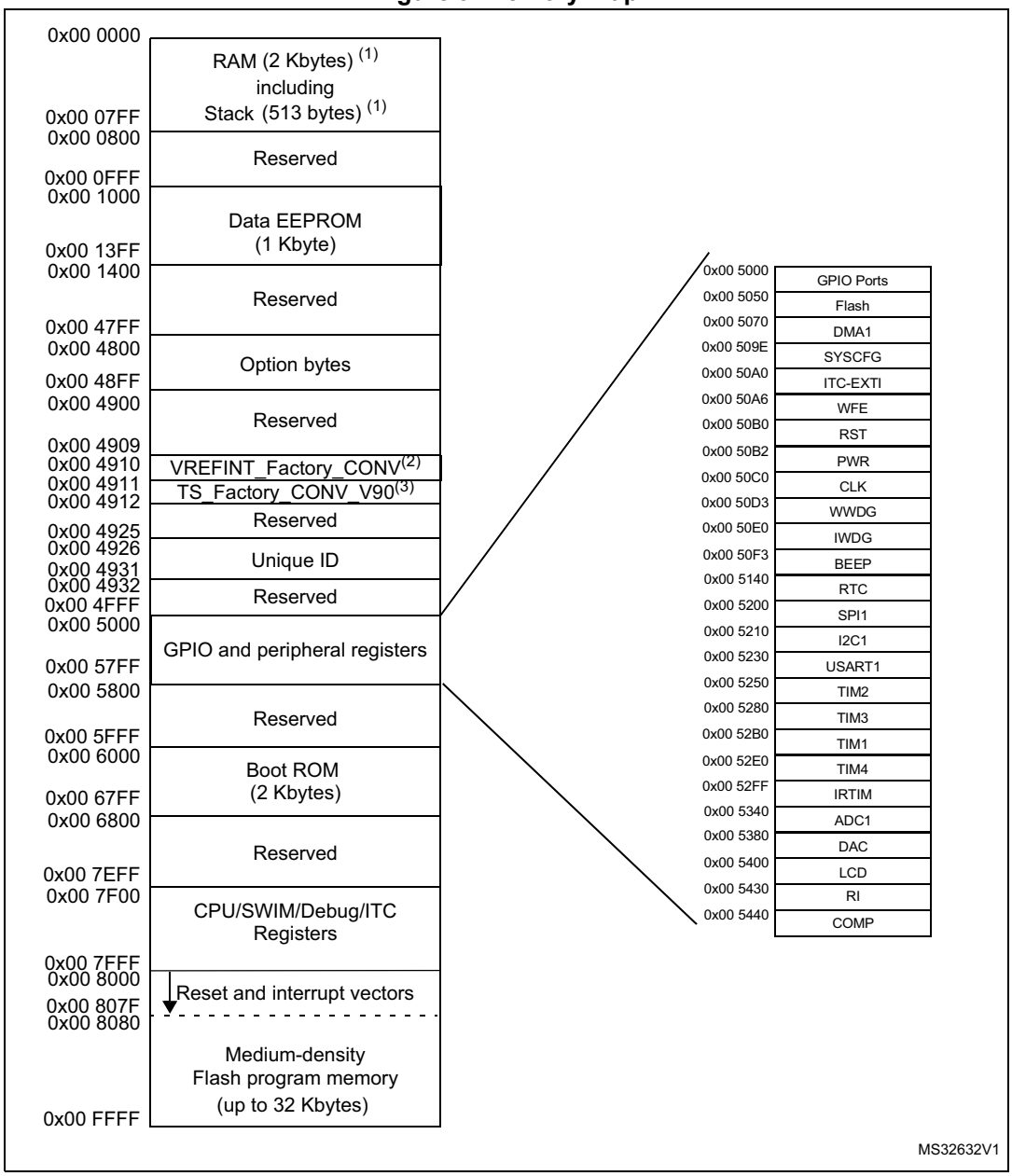
The beeper function outputs a signal on the BEEP pin for sound generation. The signal is in the range of 1, 2 or 4 kHz.

5 Memory and register map

5.1 Memory mapping

The memory map is shown in *Figure 9*.

Figure 9. Memory map



1. *Table 6* lists the boundary addresses for each memory size. The top of the stack is at the RAM end address.
2. The VREFINT_Factory_CONV byte represents the LSB of the V_{REFINT} 12-bit ADC conversion result. The MSB have a fixed value: 0x6.
3. The TS_Factory_CONV_V90 byte represents the LSB of the V_{90} 12-bit ADC conversion result. The MSB

Table 9. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 52D2	TIM1	TIM1_DCR2	TIM1 DMA1 control register 2	0x00
0x00 52D3		TIM1_DMA1R	TIM1 DMA1 address for burst mode	0x00
0x00 52D4 to 0x00 52DF	Reserved area (12 bytes)			
0x00 52E0	TIM4	TIM4_CR1	TIM4 control register 1	0x00
0x00 52E1		TIM4_CR2	TIM4 control register 2	0x00
0x00 52E2		TIM4_SMCR	TIM4 Slave mode control register	0x00
0x00 52E3		TIM4_DER	TIM4 DMA1 request enable register	0x00
0x00 52E4		TIM4_IER	TIM4 Interrupt enable register	0x00
0x00 52E5		TIM4_SR1	TIM4 status register 1	0x00
0x00 52E6		TIM4_EGR	TIM4 Event generation register	0x00
0x00 52E7		TIM4_CNTR	TIM4 counter	0x00
0x00 52E8		TIM4_PSCR	TIM4 prescaler register	0x00
0x00 52E9		TIM4_ARR	TIM4 Auto-reload register	0x00
0x00 52EA to 0x00 52FE	Reserved area (21 bytes)			
0x00 52FF	IRTIM	IR_CR	Infrared control register	0x00
0x00 5300 to 0x00 533F	Reserved area (64 bytes)			
0x00 5340	ADC1	ADC1_CR1	ADC1 configuration register 1	0x00
0x00 5341		ADC1_CR2	ADC1 configuration register 2	0x00
0x00 5342		ADC1_CR3	ADC1 configuration register 3	0x1F
0x00 5343		ADC1_SR	ADC1 status register	0x00
0x00 5344		ADC1_DRH	ADC1 data register high	0x00
0x00 5345		ADC1_DRL	ADC1 data register low	0x00
0x00 5346		ADC1_HTRH	ADC1 high threshold register high	0x0F
0x00 5347		ADC1_HTRL	ADC1 high threshold register low	0xFF
0x00 5348		ADC1_LTRH	ADC1 low threshold register high	0x00
0x00 5349		ADC1_LTRL	ADC1 low threshold register low	0x00
0x00 534A		ADC1_SQR1	ADC1 channel sequence 1 register	0x00
0x00 534B		ADC1_SQR2	ADC1 channel sequence 2 register	0x00
0x00 534C		ADC1_SQR3	ADC1 channel sequence 3 register	0x00
0x00 534D		ADC1_SQR4	ADC1 channel sequence 4 register	0x00

Table 10. CPU/SWIM/debug module/interrupt controller registers (continued)

Address	Block	Register Label	Register Name	Reset Status
0x00 7F90	DM	DM_BK1RE	DM breakpoint 1 register extended byte	0xFF
0x00 7F91		DM_BK1RH	DM breakpoint 1 register high byte	0xFF
0x00 7F92		DM_BK1RL	DM breakpoint 1 register low byte	0xFF
0x00 7F93		DM_BK2RE	DM breakpoint 2 register extended byte	0xFF
0x00 7F94		DM_BK2RH	DM breakpoint 2 register high byte	0xFF
0x00 7F95		DM_BK2RL	DM breakpoint 2 register low byte	0xFF
0x00 7F96		DM_CR1	DM Debug module control register 1	0x00
0x00 7F97		DM_CR2	DM Debug module control register 2	0x00
0x00 7F98		DM_CSR1	DM Debug module control/status register 1	0x10
0x00 7F99		DM_CSR2	DM Debug module control/status register 2	0x00
0x00 7F9A		DM_ENFCTR	DM enable function register	0xFF
0x00 7F9B to 0x00 7F9F	Reserved area (5 byte)			

1. Accessible by debug module only

Table 21. Total current consumption in Wait mode (continued)

Symbol	Parameter	Conditions[1]			Typ	Max				Unit
						55°C	85 °C[2]	105 °C (3)	125 °C (4)	
$I_{DD(Wait)}$	Supply current in Wait mode	CPU not clocked, all peripherals OFF, code executed from Flash, V_{DD} from 1.65 V to 3.6 V	HSI	f_{CPU} = 125 kHz	0.38	0.48	0.49	0.50	0.56	mA
				f_{CPU} = 1 MHz	0.41	0.49	0.51	0.53	0.59	
				f_{CPU} = 4 MHz	0.50	0.57	0.58	0.62	0.66	
				f_{CPU} = 8 MHz	0.60	0.66	0.68	0.72	0.74	
				f_{CPU} = 16 MHz	0.79	0.84	0.86	0.87	0.90	
			HSE[6] external clock (f_{CPU}=HSE)	f_{CPU} = 125 kHz	0.06	0.08	0.09	0.10	0.12	
				f_{CPU} = 1 MHz	0.10	0.17	0.18	0.19	0.22	
				f_{CPU} = 4 MHz	0.24	0.36	0.39	0.41	0.44	
				f_{CPU} = 8 MHz	0.50	0.58	0.61	0.62	0.64	
				f_{CPU} = 16 MHz	1.00	1.08	1.14	1.16	1.18	
			LSI	$f_{CPU} = f_{LSI}$	0.055	0.058	0.065	0.073	0.080	
			LSE[8] external clock (32.768 kHz)	$f_{CPU} = f_{LSE}$	0.051	0.056	0.060	0.065	0.073	

1. All peripherals OFF, V_{DD} from 1.65 V to 3.6 V, HSI internal RC osc., $f_{CPU} = f_{SYSCLK}$
2. For temperature range 6.
3. For temperature range 7.
4. For temperature range 3.
5. Flash is configured in I_{DDQ} mode in Wait mode by setting the EPM or WAITM bit in the Flash_CR1 register.
6. Oscillator bypassed (HSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the HSE consumption ($I_{DD\ HSE}$) must be added. Refer to *Table 31*.
7. Tested in production.
8. Oscillator bypassed (LSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the LSE consumption ($I_{DD\ HSE}$) must be added. Refer to *Table 32*.

Figure 15. Typ. $I_{DD(LPR)}$ vs. V_{DD} (LSI clock source)

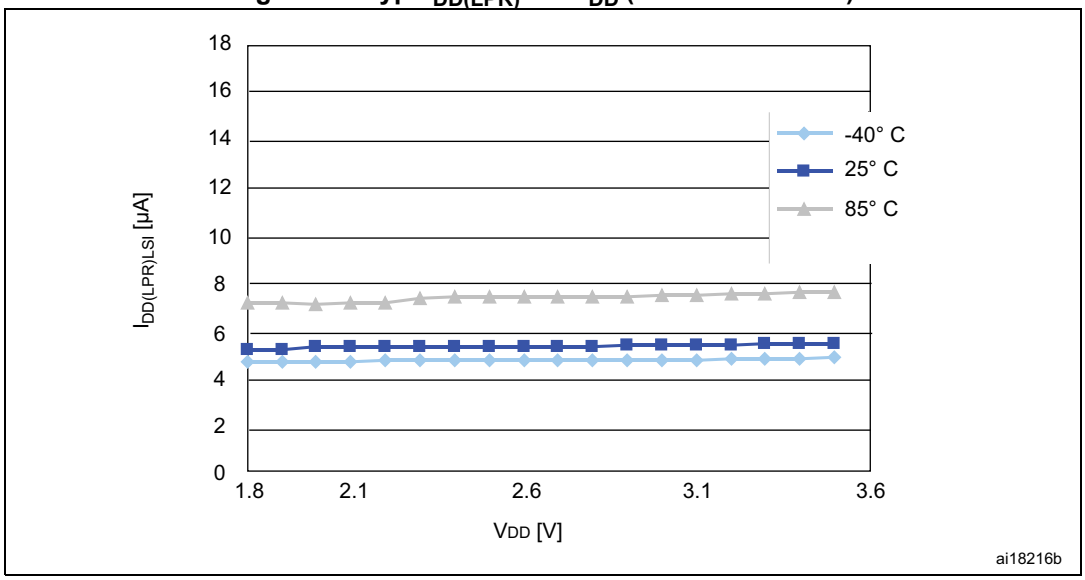
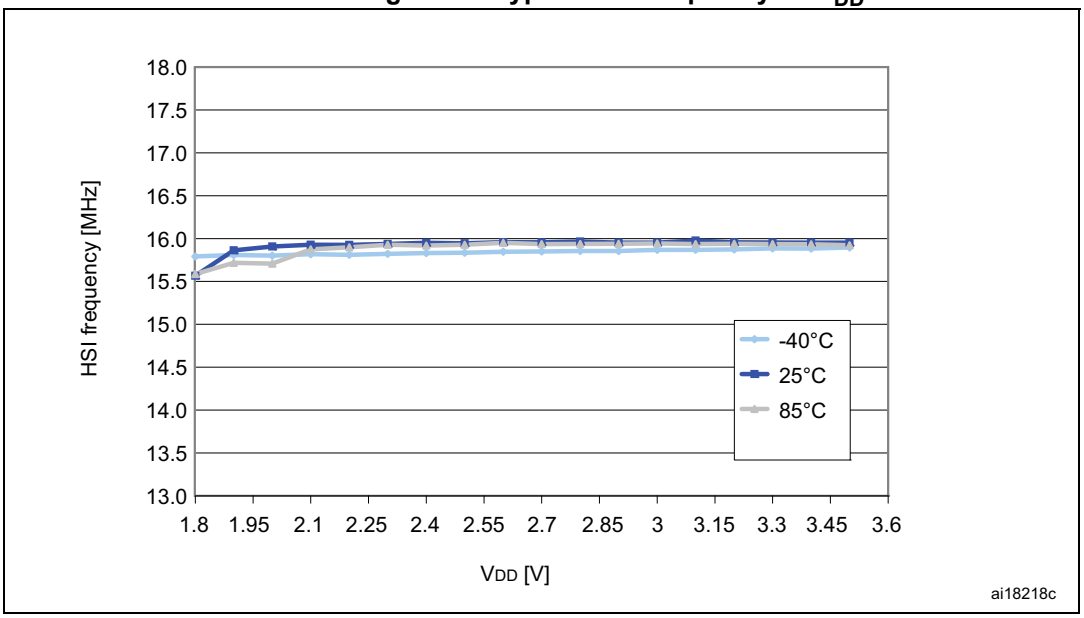


Figure 19. Typical HSI frequency vs V_{DD}



Low speed internal RC oscillator (LSI)

In the following table, data is based on characterization results, not tested in production.

Table 34. LSI oscillator characteristics

Symbol	Parameter (1)	Conditions(1)	Min	Typ	Max	Unit
f_{LSI}	Frequency	-	26	38	56	kHz
$t_{su(LSI)}$	LSI oscillator wakeup time	-	-	-	200(2)	µs
$I_{DD(LSI)}$	LSI oscillator frequency drift(3)	0 °C ≤T_A ≤85 °C	-12	-	11	%

1. V_{DD} = 1.65 V to 3.6 V, T_A = -40 to 125 °C unless otherwise specified.
2. Guaranteed by design.
3. This is a deviation for an individual part, once the initial frequency has been measured.

9.3.5 Memory characteristics

T_A = -40 to 125 °C unless otherwise specified.

Table 35. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RM}	Data retention mode (1)	Halt mode (or Reset)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Halt mode or under Reset) or in hardware registers (only in Halt mode). Guaranteed by characterization, not tested in production.

Flash memory

Table 36. Flash program and data EEPROM memory

Symbol	Parameter	Conditions	Min	Typ	Max (1)	Unit
V_{DD}	Operating voltage (all modes, read/write/erase)	f_{SYSCLK} = 16 MHz	1.65	-	3.6	V
t_{prog}	Programming time for 1 or 64 bytes (block) erase/write cycles (on programmed byte)	-	-	6	-	ms
	Programming time for 1 to 64 bytes (block) write cycles (on erased byte)	-	-	3	-	ms
I_{prog}	Programming/ erasing consumption	T_A=+25 °C, V_{DD} = 3.0 V	-	0.7	-	mA
		T_A=+25 °C, V_{DD} = 1.8 V	-	0.7	-	
t_{RET} (2)	Data retention (program memory) after 10000 erase/write cycles at T_A= –40 to +85 °C (6 suffix)	T_{RET} = +85 °C	30(1)	-	-	years
	Data retention (program memory) after 10000 erase/write cycles at T_A= –40 to +125 °C (3 suffix)	T_{RET} = +125 °C	5(1)	-	-	
	Data retention (data memory) after 300000 erase/write cycles at T_A= –40 to +85 °C (6 suffix)	T_{RET} = +85 °C	30(1)	-	-	
	Data retention (data memory) after 300000 erase/write cycles at T_A= –40 to +125 °C (3 suffix)	T_{RET} = +125 °C	5(1)	-	-	
N_{RW} (3)	Erase/write cycles (program memory)	T_A = –40 to +85 °C (6 suffix), T_A = –40 to +125 °C (3 suffix)	10(1)	-	-	kcycles
	Erase/write cycles (data memory)		300(1) (4)	-	-	

1. Data based on characterization results.
2. Conforming to JEDEC JESD22a117
3. The physical granularity of the memory is 4 bytes, so cycling is performed on 4 bytes even when a write/erase operation addresses a single byte.
4. Data based on characterization performed on the whole data memory.

6. R_{PU} pull-up equivalent resistor based on a resistive transistor (corresponding I_{PU} current characteristics described in *Figure 24*).

Figure 21. Typical V_{IL} and V_{IH} vs V_{DD} (high sink I/Os)

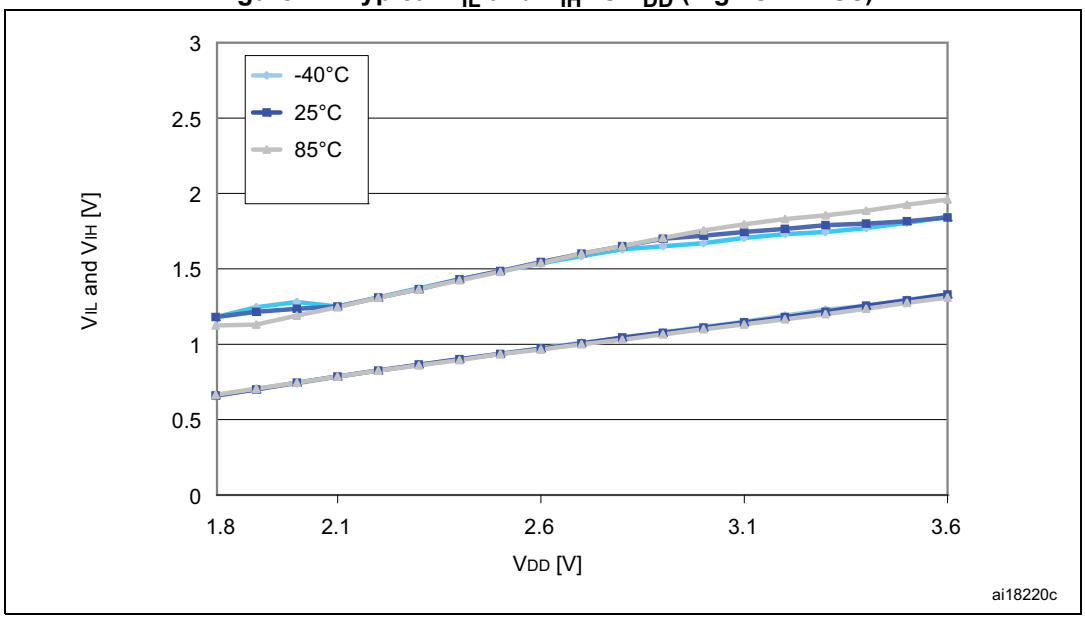
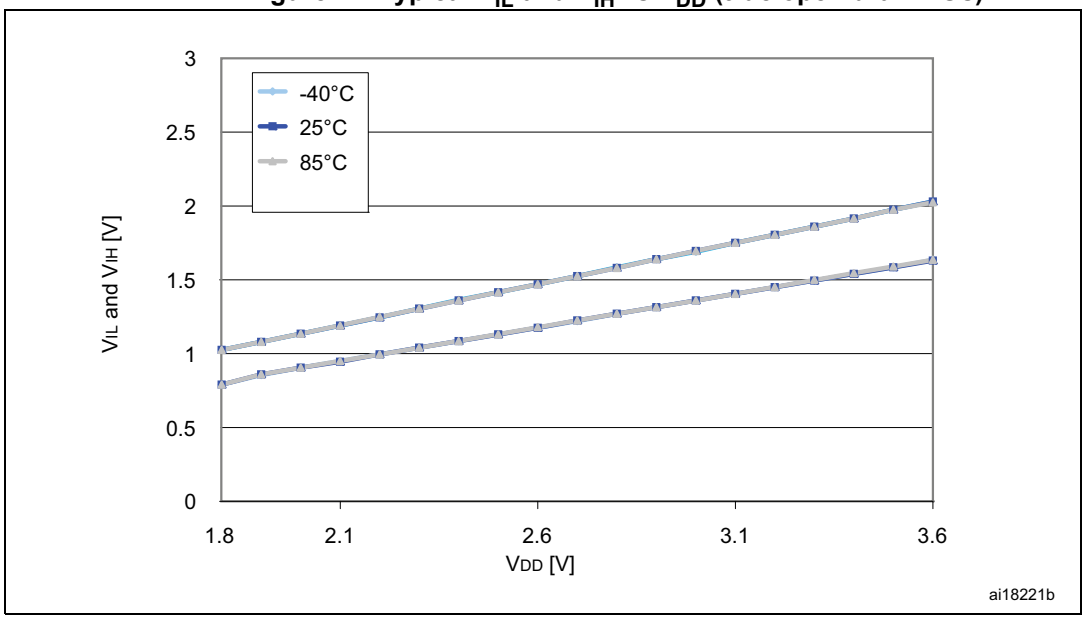


Figure 22. Typical V_{IL} and V_{IH} vs V_{DD} (true open drain I/Os)



Output driving current

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 39. Output driving current (high sink ports)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
High sink	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +2 mA, V_{DD} = 3.0 V	-	0.45	V
			I_{IO} = +2 mA, V_{DD} = 1.8 V	-	0.45	V
			I_{IO} = +10 mA, V_{DD} = 3.0 V	-	0.7	V
	V_{OH} (2)	Output high level voltage for an I/O pin	I_{IO} = -2 mA, V_{DD} = 3.0 V	V_{DD}-0.45	-	V
			I_{IO} = -1 mA, V_{DD} = 1.8 V	V_{DD}-0.45	-	V
			I_{IO} = -10 mA, V_{DD} = 3.0 V	V_{DD}-0.7	-	V

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.

Table 40. Output driving current (true open drain ports)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Open drain	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +3 mA, V_{DD} = 3.0 V	-	0.45	V
			I_{IO} = +1 mA, V_{DD} = 1.8 V	-	0.45	

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.

Table 41. Output driving current (PA0 with high sink LED driver capability)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
IR	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +20 mA, V_{DD} = 2.0 V	-	0.45	V

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.

9.3.11 Temperature sensor

In the following table, data is based on characterization results, not tested in production, unless otherwise specified.

Table 47. TS characteristics

Symbol	Parameter	Min	Typ	Max.	Unit
V_{90}(1)	Sensor reference voltage at 90°C ±5 °C,	0.580	0.597	0.614	V
T_L	V_{SENSOR} linearity with temperature	-	±1	±2	°C
Avg_slope (2)	Average slope	1.59	1.62	1.65	mV/°C
$I_{DD(TEMP)}$(2)	Consumption	-	3.4	6	µA
T_{START}(2)(3)	Temperature sensor startup time	-	-	10	µs
T_{S_TEMP}(2)	ADC sampling time when reading the temperature sensor	10	-	-	µs

1. Tested in production at V_{DD} = 3 V ±10 mV. The 8 LSB of the V_{90} ADC conversion result are stored in the TS_Factory_CONV_V90 byte.
2. Data guaranteed by design.
3. Defined for ADC output reaching its final value ±1/2LSB.

9.3.12 Comparator characteristics

In the following table, data is guaranteed by design, not tested in production, unless otherwise specified.

Table 48. Comparator 1 characteristics

Symbol	Parameter	Min	Typ	Max(1)	Unit
V_{DDA}	Analog supply voltage	1.65	-	3.6	V
T_A	Temperature range	-40	-	125	°C
R_{400K}	R_{400K} value	300	400	500	kΩ
R_{10K}	R_{10K} value	7.5	10	12.5	
V_{IN}	Comparator 1 input voltage range	0.6	-	V_{DDA}	V
V_{REFINT}	Internal reference voltage(2)	1.202	1.224	1.242	
t_{START}	Comparator startup time	-	7	10	µs
t_d	Propagation delay(3)	-	3	10	
V_{offset}	Comparator offset error	-	±3	±10	mV
I_{COMP1}	Current consumption(4)	-	160	260	nA

1. Based on characterization.
2. Tested in production at V_{DD} = 3 V ±10 mV.
3. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
4. Comparator consumption only. Internal reference voltage not included.

Table 59. EMI data (1)

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. 16 MHz	Unit
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = +25 °C, LQFP32 conforming to IEC61967-2	0.1 MHz to 30 MHz	-3	dBµV
			30 MHz to 130 MHz	9	
			130 MHz to 1 GHz	4	
			SAE EMI Level	2	-

1. Not tested in production.

Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). Two models can be simulated: human body model and charge device model. This test conforms to the JESD22-A114A/A115A standard.

Table 60. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Maximum value (1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)		500	

1. Data based on characterization results.

Static latch-up

- **LU**: 3 complementary static tests are required on 6 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

Table 61. Electrical sensitivities

Symbol	Parameter	Class
LU	Static latch-up class	II

Table 64. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package mechanical data

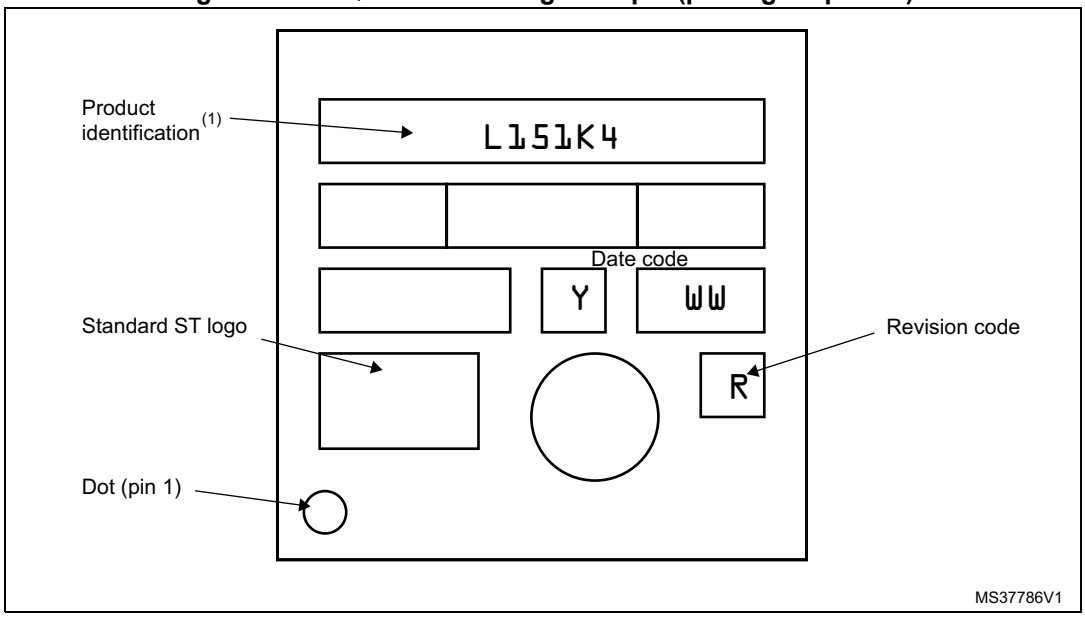
Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.300	0.370	0.450	0.0118	0.0146	0.0177
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.600	-	-	0.2205	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.600	-	-	0.2205	-
e	-	0.800	-	-	0.0315	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.100	-	-	0.0039

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location. Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 54. UFQFPN32 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

10.8 Thermal characteristics

The maximum chip junction temperature (T_{Jmax}) must never exceed the values given in *Table 18: General operating conditions on page 66*.

The maximum chip-junction temperature, T_{Jmax}, in degree Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum ambient temperature in °C
- Θ_{JA} is the package junction-to-ambient thermal resistance in °C/W
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$)
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum power dissipation on output pins
  Where:
  $P_{I/Omax} = \Sigma (V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,
  taking into account the actual V_{OL}/I_{OL} and V_{OH}/I_{OH} of the I/Os at low and high level in the application.

Table 68. Thermal characteristics(1)

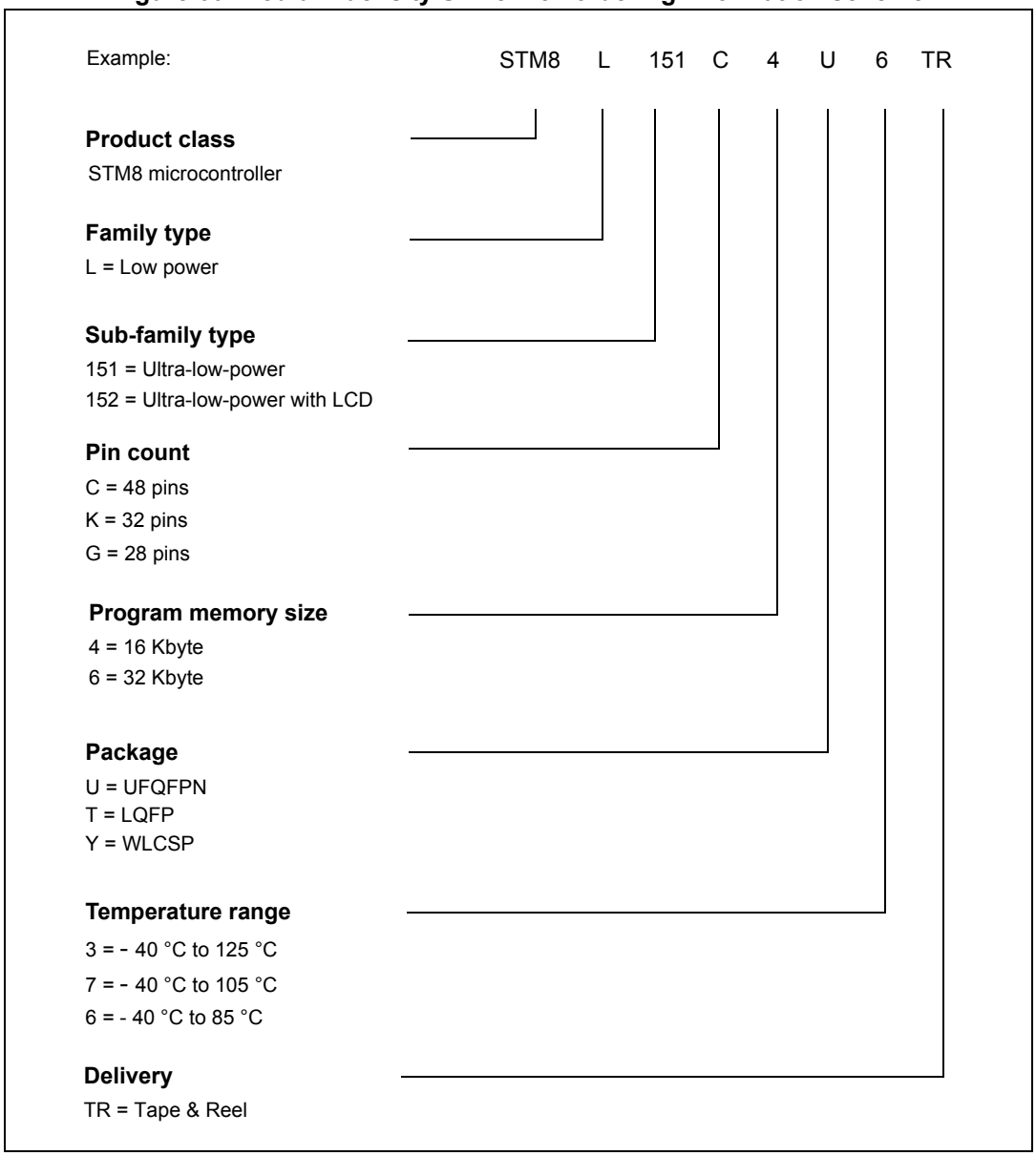
Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP 48- 7 x 7 mm	65	°C/W
Θ_{JA}	Thermal resistance junction-ambient UFQFPN 48- 7 x 7mm	32	°C/W
Θ_{JA}	Thermal resistance junction-ambient LQFP 32 - 7 x 7 mm	59	°C/W
Θ_{JA}	Thermal resistance junction-ambient UFQFPN 32 - 5 x 5 mm	38	°C/W
Θ_{JA}	Thermal resistance junction-ambient UFQFPN28 - 4 x 4 mm	118	°C/W
Θ_{JA}	Thermal resistance junction-ambient WLCSP28	70	°C/W

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

11 Part numbering

For a list of available options (memory, package, and so on) or for further information on any aspect of this device, please contact your nearest ST sales office.

Figure 60. Medium-density STM8L15x ordering information scheme



1. For a list of available options (e.g. memory size, package) and orderable part numbers or for further information on any aspect of this device, please contact the ST sales office nearest to you.

12 Revision history

Table 69. Document revision history

Date	Revision	Changes
06-Aug-2009	1	Initial release
10-Sep-2009	2	Updated peripheral naming throughout document. Added *Figure: STM8L151Cx 48-pin pinout (without LCD).* Added capacitive sensing channels in *Features.* Updated PA7, PC0 and PC1 in *Table: Medium density STM8L15x pin description.* Changed CLK and REMAP register names. Changed description of WDGHALT. Added typical power consumption values in *Table 18* to *Table 26.* Corrected VIH max value.
11-Dec-2009	3	Added WLCSP28 package Modified *Figure: Memory map* and added 2 notes. Modified Low power run mode in *Section: Low power modes.* Added *Section: Unique ID.* Modified *Table: Interrupt mapping* (added reserved area at address 0x00 8008) Modified OPT4 option bits in *Table: Option byte addresses.* *Table: Option byte description:* modified OPT0 description (“disable” instead of “enable”) and OPT1 description Added OPTBL option bytes Modified *Section: Electrical parameters.*
02-Apr-2010	4	Changed title of the document (STM8L151x4, STM8L151x6, STM8L152x4, STM8L152x6) Changed pinout (V_{SS1}, V_{DD1}, V_{SS2}, $V_{DD\ 2}$ instead of V_{SS}, $V_{DD,}$ V_{SSIO}, V_{DDIO} Changed packages Changed first page Modified note 1 in *Table: Medium density STM8L15x pin description.* Added note to PA7, PC0, PC1 and PE0 in *Table: Medium density STM8L15x pin description.* Modified *Figure: Memory map.* Modified *Table: WLCSP28 – 28-pin wafer level chip scale package, package mechanical data* (min and max columns swapped) Modified *Figure: WLCSP28 – 28-pin wafer level chip scale package, package outline* (A1 ball location) Renamed Rm, Lm and Cm EXTI_CONF replaced with EXTI_CONF1 in *Table: General hardware register map.* Updated *Section: Electrical parameters.*